

EXHIBIT D.08
U.S. Patent No. 6,853,142

References cited herein:

- U.S. Pat. No. 6,853,142 (“’142 Patent”)
- U.S. Pat. No. 6,413,382 (“Wang”)
- D.V. Mozgrin, *et al*, High-Current Low-Pressure Quasi-Stationary Discharge in a Magnetic Field: Experimental Research, Plasma Physics Reports, Vol. 21, No. 5, 1995 (“Mozgrin”)
- U.S. Pat. No. 6,398,929 (“Chiang”)

‘142 Claims 8, 17 and 18	Wang in view of Lantsman and Mozgrin
<p>[1pre.] An apparatus for generating a strongly-ionized plasma in a chamber, the apparatus comprising:</p>	<p>The combination of Wang and Lantsman discloses an apparatus for generating a strongly-ionized plasma in a chamber.</p> <p>Wang at 7:19-25 (“Preferably, the peak power P_P is at least 10 times the background power P_B, more preferably at least 100 times, and most preferably 1000 times to achieve the greatest effect of the invention. A background power P_B of 1kW will typically be sufficient to support a plasma with the torpedo magnetron and a 200 mm wafer although with little if any actual sputter deposition.”)</p> <p>Wang at 7:31-39 (“In one mode of operating the reactor, during the background period, little or no target sputtering is expected. The SIP reactor is advantageous for a low-power, low-pressure background period since the small rotating SIP magnetron can maintain a plasma at lower power and lower pressure than can a larger stationary magnetron. However, it is possible to combine highly ionized sputtering during the pulses with significant neutral sputtering during the background period.”)</p> <p>Wang at 7:28-30 (“ the application of the high peak power P_P instead quickly causes the already existing plasma to spread and increases the density of the plasma”)</p>
<p>[1a.] an ionization source that generates a weakly-ionized plasma from a feed gas, the weakly-ionized plasma reducing the probability of developing an electrical breakdown condition in the</p>	<p>The combination of Wang and Lantsman discloses an ionization source that generates a weakly-ionized plasma from a feed gas, the weakly-ionized plasma reducing the probability of developing an electrical breakdown condition in the chamber.</p> <p>Wang at Fig. 7</p>

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chamber;	<p>Wang at 4:5-6 ("A sputter working gas such as argon is supplied from a gas source 32....")</p> <p>Wang at 4:20-21 ("... a reactive gas, for example nitrogen is supplied to the processing space 22....")</p> <p>Wang at 7:17-31 ("The background power level P_B is chosen to exceed the minimum power necessary to support a plasma... [T]he application of the high peak power P_P quickly causes the already existing plasma to spread and increases the density of the plasma.")</p> <p>Wang at 7:19-25 ("Preferably, the peak power P_P is at least 10 times the background power P_B ... and most preferably 1000 times to achieve the greatest effect of the invention. A background power P_B of 1 kW [causes] little if any actual sputter deposition.")</p> <p>Wang at 4:23-31 (Ex. 1005) ("...thus creating a region 42 of a high-density plasma (HDP)...")</p> <p>Wang at 7:3-49 ("Plasma ignition, particularly in plasma sputter reactors, has a tendency to generate particles during the initial arcing, which may dislodge large particles from the target or chamber... The initial plasma ignition needs be performed only once and at much lower power levels so that particulates produced by arcing are much reduced.")</p> <p>Wang at 7:25-28 ("As a result, once the plasma has been ignited at the beginning of sputtering prior to the illustrated waveform, no more plasma ignition occurs.").</p> <p>Wang at 7:58-61 ("... DC power supply 100 is connected to the target 14 ... and supplies an essentially constant negative voltage to the target 14 corresponding to the background power P_B.")</p> <p>Wang at 7:22-23 ("A background power P_B of 1 kW will typically be sufficient to support a plasma...")</p>
[1b.] a power supply that supplies power to the weakly-ionized plasma though an electrical pulse applied across	The combination of Wang and Lantsman discloses a power supply that supplies power to the weakly-ionized plasma though an electrical pulse applied across the weakly-ionized plasma, the electrical pulse having a magnitude and a rise-

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<p>the weakly-ionized plasma, the electrical pulse having a magnitude and a rise-time that is sufficient to increase the density of the weakly-ionized plasma to generate a strongly-ionized plasma; and</p>	<p>time that is sufficient to increase the density of the weakly-ionized plasma to generate a strongly-ionized plasma.</p> <p>Wang at Fig. 7</p> <p>Wang at 7:61-62 ("The pulsed DC power supply 80 produces a train of negative voltage pulses.")</p> <p>Wang at 7:19-25 ("Preferably, the peak power level P_P is at least 10 times the background power level P_B, ... most preferably 1000 times to achieve the greatest effects of the invention. A background power P_B of 1 kW will typically be sufficient...")</p> <p>Wang at 7:28-30 ("... the application of the high peak power P_P instead quickly causes the already existing plasma to spread and increases the density of the plasma.")</p> <p>Wang at 7:36-39 ("However, it is possible to combine highly ionized sputtering during the pulses with significant neutral sputtering during the background period.")</p> <p>Wang at 5:23-27 ("[The pulse's] exact shape depends on the design of the pulsed DC power supply 80, and significant rise times and fall times are expected.")</p> <p><i>See evidence cited in limitation [1pre] of claim 1.</i></p>
<p>[1c.] a gas line that supplies feed gas to the strongly-ionized plasma, the feed gas diffusing the strongly-ionized plasma, thereby allowing additional power from the pulsed power supply to be absorbed by the strongly-ionized plasma.</p>	<p>The combination of Wang and Lantsman discloses a gas line that supplies feed gas to the strongly-ionized plasma, the feed gas diffusing the strongly-ionized plasma, thereby allowing additional power from the pulsed power supply to be absorbed by the strongly-ionized plasma.</p> <p>Wang at Fig. 1</p> <p>Wang at 4:5-6 ("A sputter working gas such as argon is supplied from a gas source 32 through a mass flow controller 34 to a region in back of the grounded shield 24.")</p> <p>Wang at 4:8-10 ("The gas flows into the processing region 22 through a gap formed between the pedestal 18, the grounded shield 24, and a clamp ring or plasma focus ring 36 surrounding the periphery of the wafer 20.")</p>

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	<p>Wang at 4:51-55 ("A computerized controller 58 controls the ... mass flow controller 34, as illustrated....")</p> <p>Lantsman at 2:48-51 ("This secondary power supply 'pre-ignites' the plasma so that when the primary power supply is applied, the system smoothly transitions to final plasma development and deposition.")</p> <p>One of ordinary skill would have been motivated to combine Wang and Lantsman. Lantsman is directed to sputtering using a plasma. So is Wang. <i>See</i> Wang at Title ("Pulsed sputtering with a small rotating magnetron"); 3:20-21 ("[A] high plasma density is achieved adjacent to the magnetron during the pulse."). Also, Lantsman uses two power supplies, one for pre-ionization and one for deposition. So does Wang. <i>See</i> Wang at Fig. 7 [<i>showing pulsed supply 80 and constant supply 100</i>]</p> <p>Lantsman generates a plasma without arcing. So does Wang. Wang at 7:3-49 ("Plasma ignition, particularly in plasma sputter reactors, has a tendency to generate particles during the initial arcing, The initial plasma ignition needs be performed only once and at much lower power levels so that particulates produced by arcing are much reduced.")</p> <p>Summarizing, Wang and Lantsman relate to the same application. Further, one of ordinary skill would have been motivated to use Lantsman's continuous gas flow in Wang so as to maintain a desired pressure in the chamber. Also, use of Lantsman's continuous gas flow in Wang would have worked well with Wang's mass flow controller 34 and would have been a combination of old elements in which each element behaved as expected. Finally, such a continuous flow of gas in Wang would diffuse the strongly-ionized plasma and allow additional power to be absorbed by the plasma as required by claim 40.</p>
<p>7. The apparatus of claim 1 further comprising a magnet that is positioned to generate a magnetic field proximate to the weakly-ionized plasma, the magnetic field trapping electrons in the weakly-ionized</p>	<p>The combination of Wang and Lantsman discloses a magnet that is positioned to generate a magnetic field proximate to the weakly-ionized plasma, the magnetic field trapping electrons in the weakly-ionized plasma.</p> <p><i>See</i> evidence cited in claim 1</p> <p>'142 Patent at 1:41-43 [<i>in the Background of the Invention</i>]</p>

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plasma.	<p>("Magnetron sputtering systems use magnetic fields that are shaped to trap and concentrate secondary electrons....")</p> <p>Wang at 4:23-31 ("A small rotatable magnetron 40 is thus creating a region 42 of a high-density plasma (HDP)....")</p> <p>Wang at Fig. 1</p>
8. The apparatus of claim 7 wherein the magnet comprises an electro-magnet.	<p>The combination of Wang, Lantsman and Mozgrin discloses the magnet comprises an electro-magnet.</p> <p><i>See evidence cited in claim 7</i></p> <p>Mozgrin at Fig. 1</p> <p>Mozgrin at 401, right col, Fig. 1 caption, ("Fig. 1. Discharge device configurations: (a) planar magnetron; (b) shaped-electrode configuration....")</p> <p>Mozgrin at 401, left col, ¶ 2 ("The system with shaped electrodes involved two axisymmetrical electrodes 120 mm in diameter separated by about 10 mm, and immersed in a cusp-shaped magnetic field produced by oppositely directed multilayer coils. The values of B_{\max} were controlled by coil current variation to range from 0 to 1000 G.") (emphasis added)</p>
[10pre.] A method for generating a strongly-ionized plasma in a chamber, the method comprising:	<p>The combination of Wang and Lantsman discloses a method for generating a strongly-ionized plasma in a chamber.</p> <p><i>See evidence cited in claim 1 preamble.</i></p>
[10a.] ionizing a feed gas to form a weakly-ionized plasma that reduces the probability of developing an electrical breakdown condition in the chamber;	<p>The combination of Wang and Lantsman discloses ionizing a feed gas to form a weakly-ionized plasma that reduces the probability of developing an electrical breakdown condition in the chamber.</p> <p><i>See evidence cited limitation [1a] in claim 1.</i></p>
[10b.] supplying power to the weakly-ionized plasma by applying an electrical pulse across the weakly-ionized plasma, the electrical pulse having a magnitude and a rise-	<p>The combination of Wang and Lantsman discloses supplying power to the weakly-ionized plasma by applying an electrical pulse across the weakly-ionized plasma, the electrical pulse having a magnitude and a rise-time that is sufficient to increase the density of the weakly-ionized</p>

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time that is sufficient to increase the density of the weakly-ionized plasma to generate a strongly-ionized plasma; and	plasma to generate a strongly-ionized plasma. <i>See</i> evidence cited in limitation [1b] in claim 1.
[10c.] diffusing the strongly-ionized plasma with additional feed gas thereby allowing the strongly-ionized plasma to absorb additional energy from the power supply.	The combination of Wang and Lantsman discloses diffusing the strongly-ionized plasma with additional feed gas thereby allowing the strongly-ionized plasma to absorb additional energy from the power supply. <i>See</i> evidence cited in limitation [1c] in claim 1.
17. The method of claim 10 wherein the peak plasma density of the weakly-ionized plasma is less than about 10^{12} cm^{-3} .	The combination of Wang, Lantsman and Mozgrin discloses the peak plasma density of the weakly-ionized plasma is less than about 10^{12} cm^{-3} . <i>See</i> evidence cited in claim 10 Mozgrin at 401 (“We found out that only the regimes with magnetic field strength not lower than 400 G provided the initial plasma density in the 10^9 - 10^{11} cm^{-3} range.”) One of ordinary skill would expect Wang’s background plasma to have a density comparable to that of Mozgrin’s region 1. Mozgrin’s region 1 and Wang’s background power level, P_B , are both used to generate base plasmas prior to application of a pulse. In both Wang and Mozgrin, application of the pulse increases the density of the plasma and the resulting high density plasma can then be used for sputtering. One of ordinary skill would expect Wang’s pre-pulse plasma (generated with P_B) to have a density similar to that of Mozgrin’s pre-pulse plasma. Mozgrin’s pre-pulse plasma, in Mozgrin’s region 1, has a density that is below 10^{12} cm^{-3} .
18. The method of claim 10 wherein the peak plasma density of the strongly-ionized plasma is greater than about 10^{12} cm^{-3} .	The combination of Wang, Lantsman and Mozgrin discloses the peak plasma density of the strongly-ionized plasma is greater than about 10^{12} cm^{-3} . <i>See</i> evidence cited in claim 10 Wang at 7:28-30 (“the <i>application of the high peak power P_P</i> instead quickly causes the already existing plasma to

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	<p>spread and <i>increases the density of the plasma</i>").</p> <p>Wang at 4:29-31 ("increases the sputtering rate but also at sufficiently high density ionizes a substantial fraction of the sputtered particles into positively charged metal ions.")</p> <p>Mozgrin at 403, right col, ¶4 ("Regime 2 was characterized by intense cathode sputtering....").</p> <p>Mozgrin at 409, left col, ¶ 4 ("The implementation of the high-current magnetron discharge (regime 2) in sputtering ... plasma density (exceeding $2 \times 10^{13} \text{ cm}^{-3}$).")</p> <p>A person of ordinary skill would expect Wang's sputtering plasma, generated with the peak power, P_p, to have a density similar to that of the plasma in Mozgrin's region 2, which Mozgrin uses for sputtering. Wang and Mozgrin both disclose using pulses to increase the density of a plasma for sputtering. Accordingly, one of ordinary skill reading Wang would have looked to Mozgrin to determine actual plasma densities. The density in Mozgrin's region 2 was greater than 10^{12} cm^{-3}.</p> <p><u>Background:</u></p> <p>Chiang ['929 Patent] at 3:42-47 ("A high-density plasma is defined as one having an average plasma density across the plasma, exclusive of the plasma sheaths, of at least 10^{11} cm^{-3}, and preferably at least 10^{12} cm^{-3}.")</p>